



Fast Recovery Epitaxial Diode (FRED) Modules

MEA 160-06DA
MEE 160-06DA
MEK 160-06DA

$I_{FAVM} = 162 \text{ A}$
 $V_{RRM} = 600 \text{ V}$
 $t_{rr} = 250 \text{ ns}$

Preliminary data

V_{RSM} V	V_{RRM} V	Type	MEA 160-06DA	MEE 160-06DA	MEK 160-06DA
600	600		1 2 3	2 1 3	1 2 3

Symbol	Test Conditions	Maximum Ratings	
I_{FRMS}	$T_{VJ} = 125^\circ\text{C}; T_s = 65^\circ\text{C}$	229	A
I_{FAVM} ①	$T_{VJ} = 125^\circ\text{C}; T_s = 65^\circ\text{C}; \text{rectangular, } d = 0.5$	162	A
I_{FM}	$T_{VJ} = 125^\circ\text{C}; T_s = 65^\circ\text{C}$	650	A
I_{FSM}	$T_{VJ} = 45^\circ\text{C}; t = 10 \text{ ms (50 Hz), sine}$ $t = 8.3 \text{ ms (60 Hz), sine}$	1200	A
		1280	A
	$T_{VJ} = 150^\circ\text{C}; t = 10 \text{ ms (50 Hz), sine}$ $t = 8.3 \text{ ms (60 Hz), sine}$	1080	A
		1190	A
$\int i^2 dt$	$T_{VJ} = 45^\circ\text{C} t = 10 \text{ ms (50 Hz), sine}$ $t = 8.3 \text{ ms (60 Hz), sine}$	7200	A ² s
		6800	A ² s
	$T_{VJ} = 150^\circ\text{C}; t = 10 \text{ ms (50 Hz), sine}$ $t = 8.3 \text{ ms (60 Hz), sine}$	5800	A ² s
		5900	A ² s

T_{VJ}	-40...+150	°C
T_{atg}	-40...+125	°C
T_{Smax}	110	°C

P_{tot}	$T_s = 25^\circ\text{C}; T_{VJ} = 150^\circ\text{C}$	500	W
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V_{ISOL}	50/60 Hz, RMS $t = 1 \text{ min}$	3000	V~
	$I_{ISOL} \leq 1 \text{ mA} t = 1 \text{ s}$	3600	V~

M_d	Mounting torque (M6)	2.25-2.75/20-25	Nm/lb.in.
	Terminal connection torque (M6)	4.5-5.5/40-48	Nm/lb.in.

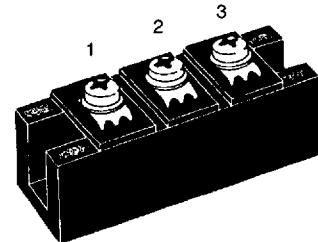
d_s	Creeping distance on surface	12.7	mm
d_A	Strike distance through air	9.6	mm
a	Maximum allowable acceleration	50	m/s ²

Weight	150	g
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Symbol	Test Conditions	Characteristic Values	
		typ.	max.
I_R	$T_{VJ} = 25^\circ\text{C}$ $V_R = V_{RRM}$	12	mA
	$T_{VJ} = 25^\circ\text{C}$ $V_R = 0.8 \cdot V_{RRM}$	3	mA
	$T_{VJ} = 125^\circ\text{C}$ $V_R = 0.8 \cdot V_{RRM}$	60	mA
V_F	$I_F = 150 \text{ A}; T_{VJ} = 125^\circ\text{C}$	1.20	V
	$T_{VJ} = 25^\circ\text{C}$	1.42	V
	$I_F = 260 \text{ A}; T_{VJ} = 125^\circ\text{C}$	0.87	V
	$T_{VJ} = 25^\circ\text{C}$	1.56	V
V_{TO}	For power-loss calculations only	0.87	V
r_T	$T_{VJ} = 125^\circ\text{C}; I_{F1} = 150 \text{ A}; I_{F2} = 260 \text{ A}$	1.98	mΩ
R_{thJS}		0.228	K/W
t_{rr}	$I_F = 150 \text{ A}$	250	ns
I_{RM}	$V_R = 300 \text{ V}$	28	A
	$-di/dt = 400 \text{ A}/\mu\text{s}$	42	A

① I_{FAVM} rating includes reverse blocking losses at T_{VJM} , $V_R = 0.6 V_{RRM}$, duty cycle $d = 0.5$
Data according to DIN/IEC 747

IXYS reserves the right to change limits, test conditions and dimensions



Features

- International standard package with DCB ceramic base plate
- Planar passivated chips
- Short recovery time
- Low switching losses
- Soft recovery behaviour
- Isolation voltage 3600 V~
- UL registered E 72873

Applications

- Antiparallel diode for high frequency switching devices
- Free wheeling diode in converters and motor control circuits
- Inductive heating and melting
- Uninterruptible power supplies (UPS)
- Ultrasonic cleaners and welders

Advantages

- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching
- Low losses

Dimensions in mm (1 mm = 0.0394")

